



骏业（香港）实业有限公司

400-0744-078

SOT-323 Plastic-Encapsulate Transistors

S9014W TRANSISTOR (NPN)

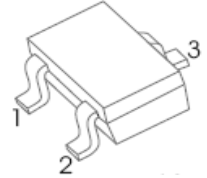
FEATURES

- Complementary to S9015W
- Small Surface Mount Package

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	100	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

SOT - 323



1. BASE
2. EMITTER
3. COLLECTOR

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=100\mu\text{A}$, $I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}$, $I_E=0$			100	nA
Collector cut-off current	I_{CEO}	$V_{CE}=35\text{V}$, $I_B=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}$, $I_C=0$			100	nA
DC current gain	h_{FE}	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$	200		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}$, $I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}$, $I_B=5\text{mA}$			1	V
Base-emitter voltage	V_{BE}	$V_{CE}=5\text{V}$, $I_C=2\text{mA}$	0.58		0.7	V
Transition frequency	f_T	$V_{CE}=5\text{V}$, $I_C=10\text{mA}$, $f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$			3.5	pF

CLASSIFICATION OF h_{FE}

RANK	L	H
RANGE	200 - 450	450 - 1000
MARKING	J6	